

Sn. 09/844,481

Attorney Docket No. FUJI:185

IN THE CLAIMS

The status of the claims as presently amended is as follows (changes highlighted):

1. (Canceled)

2. (Currently Amended) A lateral semiconductor device comprising:

a semiconductor chip;

two main electrodes on one major surface of the semiconductor chip; and

an alternating conductivity type layer between the main electrodes;

wherein the alternating conductivity type layer comprises first semiconductor regions of a first conductivity type and second semiconductor regions of a second conductivity type;

wherein the first semiconductor regions and the second semiconductor regions are alternately arranged;

wherein the alternating conductivity type layer comprises a closed loop surrounding one of the main electrodes;

wherein the alternating conductivity type layer comprises first and second sections, wherein the first semiconductor regions and the second semiconductor regions are arranged alternately at a first pitch in the first section, and the first semiconductor regions and the second semiconductor regions are arranged alternately at a second pitch different from the first pitch in the second section; and

wherein ~~the closed loop is formed in a laminated direction of the first semiconductor regions and the second semiconductor regions, and~~ a lateral width of the first semiconductor regions and the second semiconductor regions forming the closed loop is the same.

3-5. (Canceled)

6. (Currently Amended) A lateral semiconductor device comprising:

a semiconductor chip;

two main electrodes on one major surface of the semiconductor chip; and

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an alternating conductivity type layer between the main electrodes;
wherein the alternating conductivity type layer comprises first semiconductor regions of a first conductivity type and second semiconductor regions of a second conductivity type;
wherein the first semiconductor regions and the second semiconductor regions are alternately arranged;
wherein the alternating conductivity type layer comprises a closed loop surrounding one of the main electrodes;
wherein the alternating conductivity type layer comprises at least one straight section and at least one curved section;
wherein the first semiconductor regions and the second semiconductor regions are arranged alternately at a first pitch in the straight section, and the first semiconductor regions and the second semiconductor regions are arranged alternately at a second pitch in the curved section, the second pitch being different from the first pitch; and
wherein ~~the closed loop is formed in a laminated direction of the first semiconductor regions and the second semiconductor regions, and a lateral width of the first semiconductor regions and the second semiconductor regions forming the closed loop in the straight section is the same.~~

7. *(Currently Amended)* The lateral semiconductor device according to Claim 6, wherein the first pitch is ~~equal to or~~ longer than the second pitch.

8. *(Previously Amended)* The lateral semiconductor device according to Claim 6, wherein the curved section is doped substantially more lightly than the straight section.

9. *(Previously Amended)* The lateral semiconductor device according to Claim 8, wherein the curved section is substantially intrinsic.

10. *(Original)* The lateral semiconductor device according to Claim 8, wherein the first pitch is

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shorter than the second pitch.

11. *(Previously Amended)* The lateral semiconductor device according to Claim 8, wherein the curved section is doped with an n-type impurity and a p-type impurity.

12. *(Previously Amended)* The lateral semiconductor device according to Claim 9, wherein the curved section is doped with an n-type impurity and a p-type impurity.

13. *(Previously Amended)* The lateral semiconductor device according to Claim 6, wherein the lateral width of at least a portion of the curved section is larger than the lateral width of the straight section.

14-34. *(Canceled)*